Abstract of the Disclosure

A light emitting device includes a silicon substrate (1), a silicon nitride film (2) formed on the surface of the silicon substrate (1), at least an n-type layer (3), (4) and a p-type layer (6), (7) which are formed on the silicon nitride film (2) and also which are made of a ZnO based compound semiconductor, and a semiconductor layer lamination (11) in which layers are laminated to form a light emitting layer. Preferably this silicon nitride film (2) is formed by thermal treatment conducted in an atmosphere containing nitrogen such as an ammonium gas. Also, in another embodiment, a light emitting device is formed by growing a ZnO based compound semiconductor layer on a main face of a sapphire substrate, the main face being perpendicular to the C-face thereof. As a result, it is possible to obtain a device using a ZnO based compound with high properties such as an LED very excellent in crystallinity and having a high light emitting efficiency.